MANOFAB

Nanofab®

CVD/PECVD tools for growth of 1D/2D nanomaterials and heterostructures





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The Business of Science®

Nanofab

CVD, PECVD and ICP CVD systems for growth of nanomaterials

lanostructured materials and **PECVD films**

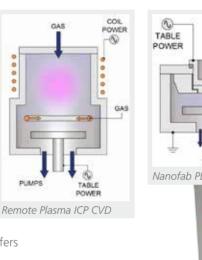
Chemical Vapour Deposition (CVD) techniques form the workhorse for research on nanomaterials. The flexibility of this technique allows deposition down to atomic layers as well as thicker films.

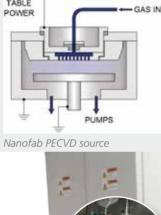
The Nanofab delivers high performance growth of nanomaterials with in-situ catalyst activation and rigorous process control.

- Cold wall design with showerhead based uniform precursor delivery
- Remote plasma via ICP option
- Vacuum load lock for quick sample exchange
- Excellent temperature uniformity
- Optional liquid/solid source delivery system for growth of MoS₂, MoSe₂ and other TMDCs
- Variable sample sizes up to maximum 200mm wafers
- Multiple view ports for diagnostics

Scalable production via a clustered tool assembly





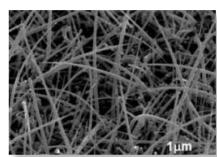




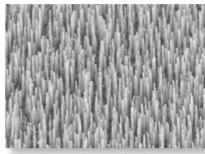
Inside view of precursor pot for liquid/ solid precursors. Example: Mo(CO)_e W(CO)₆ DMDS, DESe, DETe etc.

Processes

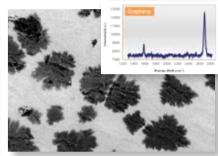
CVD, PECVD and ICP CVD



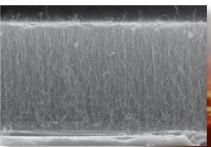
Au nanoparticle catalysts



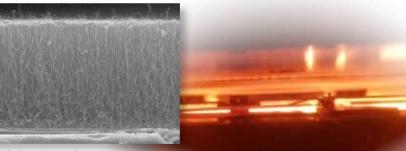
precursors. (Courtesy of Nanoscience Centre, Uni



(Growth arrested before film completion to visualise domains in SEM)

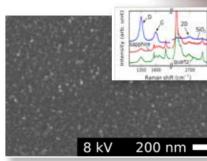


grown by PECVD



Dense Carbon Nanotubes

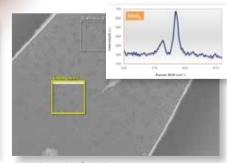




PECVD of nanocrystalline Graphene on SiO (Courtesy of Southampton Uni)



PECVD of vertically aligned graphene. (Courtesy of IMEC, Belgium)



CVD Growth of MoS.

	700°C table	800°C table	1200°C table
Thin Film Process	SiO _x , SiN _x , aSiC, aSi, μc-Si, polySi*	SiO _x , SiN _x , aSiC, aSi, μc-Si, polySi	SiO _x , SiN _x , aSiC, aSi, μc-Si, polySi
1D Nanomaterials	MWNTs, Si, Ge NWs, ZnO NWs	MWNTs, SWNTs*, Si, Ge NWs	MWNTs, SWNTs, Si, Ge NWs
2D Nanomaterials	NA	Nano- crystalline Graphene, Vertical Graphene	Graphene, hBN, MoS ₂ /WS ₂ , Vertical Graphene, Nano-crystalline Graphene

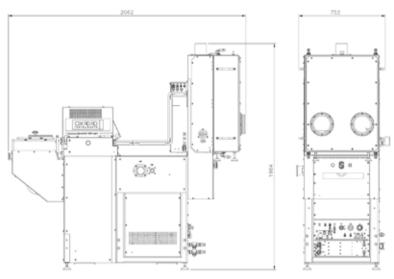


Technical Specifications

For further information about our Nanofab range, please contact your local Oxford Instruments Office

AB

Nanofab dimensions All dimensions in mm



Customer support & training

Our range of service level agreements will be tailored to your needs:

- Choice of support coverage up to 24/7
- Scheduled preventative maintenance calls
- Managed spares inventory options
- Preferential spare part pricing
- Process & user maintenance training
- Guaranteed response times for support engineer visits and technical hotline calls

Oxford Instruments Plasma Technology

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